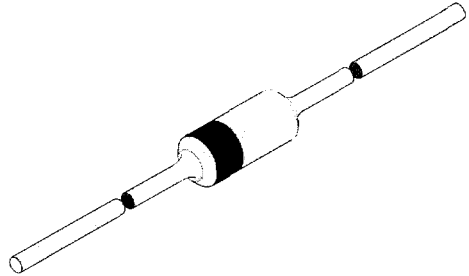




Silicon Planar Diodes

Features

- Low differential forward resistance
- Low diode capacitance
- High reverse impedance



94 9367

Applications

Band switching in VHF-tuners

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage			V_R	35	V
Forward current			I_F	100	mA
Junction temperature			T_j	150	$^\circ\text{C}$
Storage temperature range			T_{stg}	-55...+150	$^\circ\text{C}$

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4\text{mm}, T_L=\text{constant}$	R_{thJA}	350	K/W

BA282.BA283

Vishay Telefunken



Electrical Characteristics

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=100\text{mA}$		V_F			1	V
Reverse current	$V_R=20\text{V}$		I_R			50	nA
Diode capacitance	$f=100\text{MHz}, V_R=1\text{V}$		C_D			1.5	pF
	$f=100\text{MHz}, V_R=3\text{V}$	BA282	C_D			1.25	pF
Differential forward resistance	$f=200\text{MHz}, I_F=3\text{mA}$	BA282	r_f			0.7	Ω
		BA283	r_f			1.2	Ω
	$f=200\text{MHz}, I_F=10\text{mA}$	BA282	r_f			0.5	Ω
		BA283	r_f			0.9	Ω
Reverse impedance	$f=100\text{MHz}, V_R=1\text{V}$		Z_r	100			k Ω

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

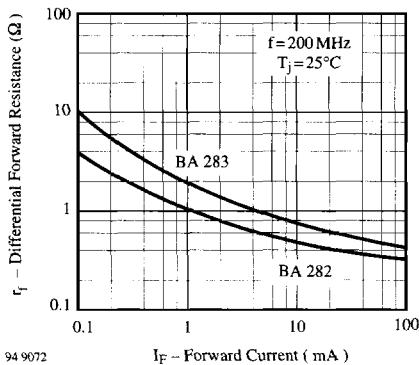


Figure 1. Differential Forward Resistance vs. Forward Current

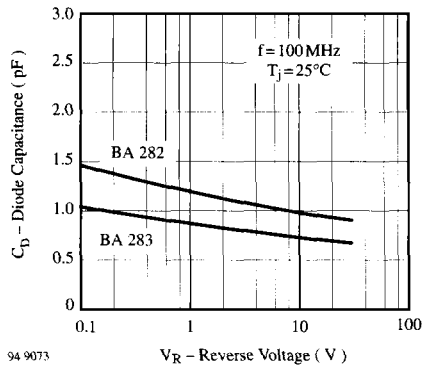


Figure 2. Diode Capacitance vs. Reverse Voltage

Dimensions in mm

technical drawings according to DIN specifications

94 9366

Standard Glass Case
54 A 2 DIN 41880
JEDEC DO 35
Weight max. 0.3 g

